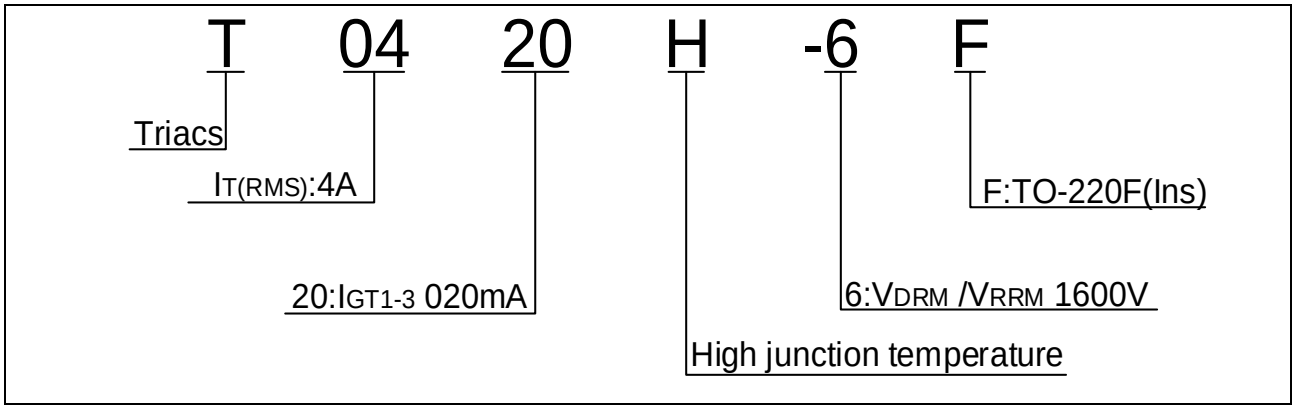
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	20	mA

V_D =V


T
04
20
H
-6
F
Triacs
IT(RMS):4A
20:IGT1-3 020mA
High junction temperature
6:VDRM /VRRM 1600V
F:TO-220F(Ins)

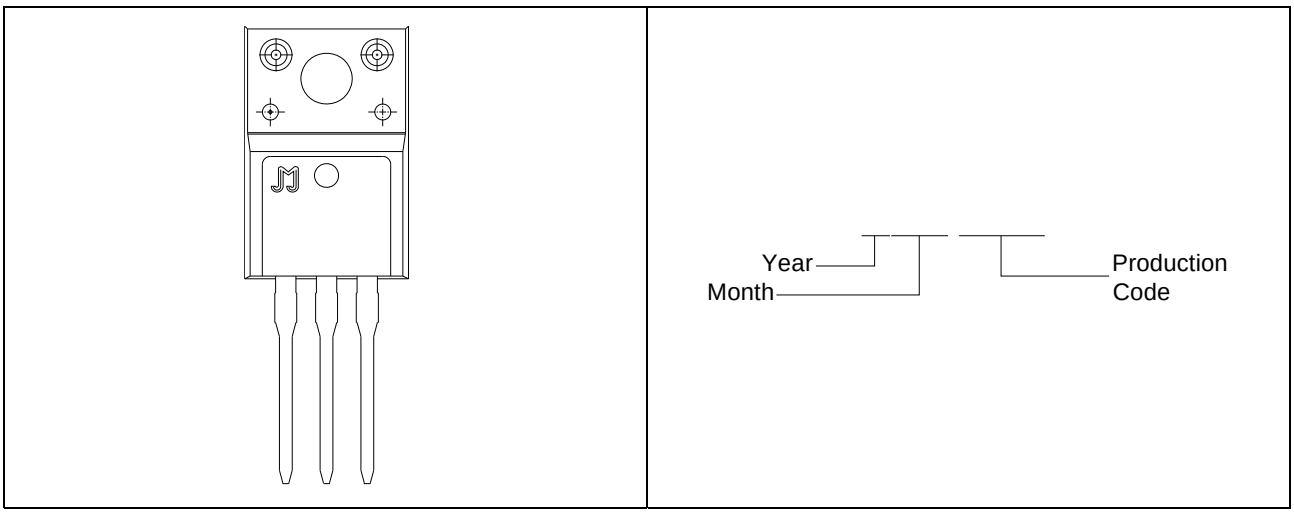
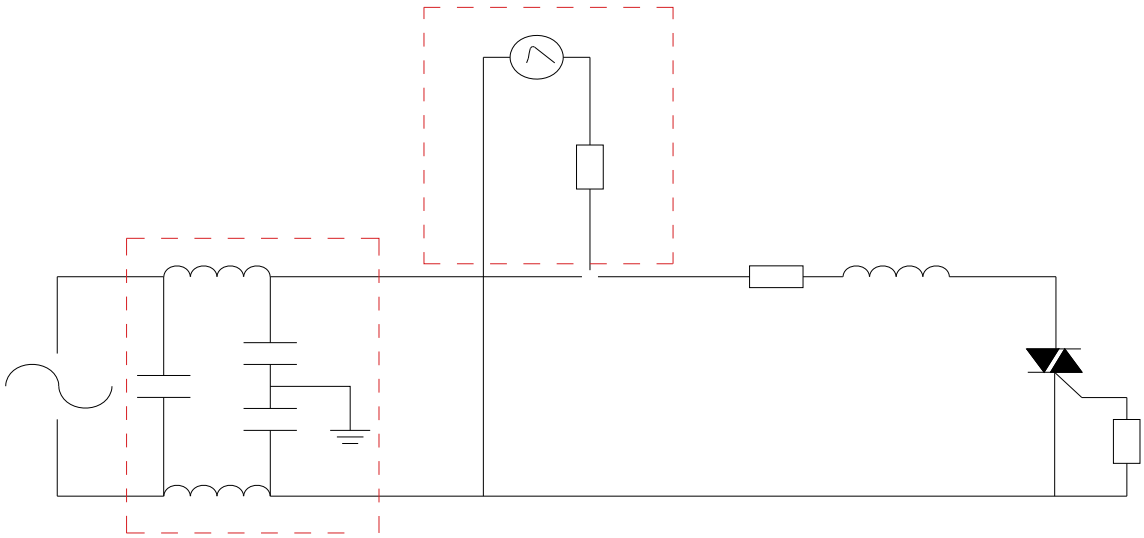

Year
Month
Production
Code

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



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